Min.	Typ.	Max.	Unit	Test condition
	1433		pF	V_{GS}=0 V, V_{DS}=50 V, ¦ 00 kHz
	92.5		pF	
	3.9		pF	

Turn-on deA7 1.304 645.1 148.1

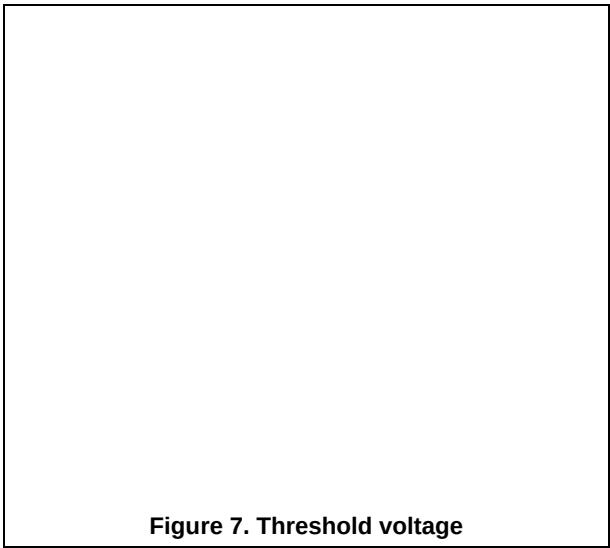


Figure 7. Threshold voltage

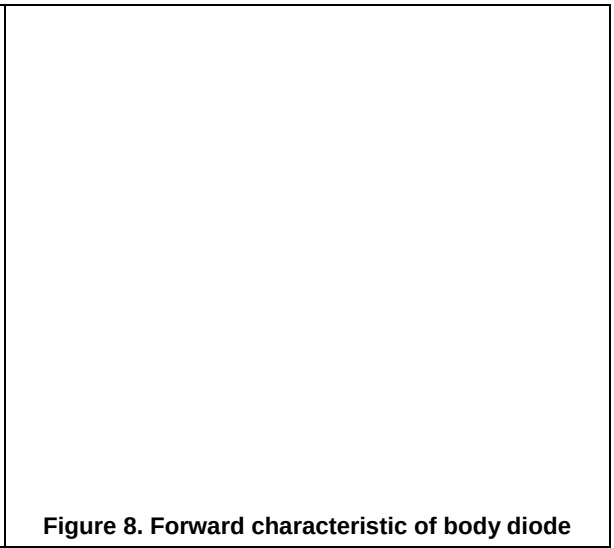


Figure 8. Forward characteristic of body diode

Figure 9. Drain-source on-state resistance

Figure 10. Drain current

Test circuits and waveforms

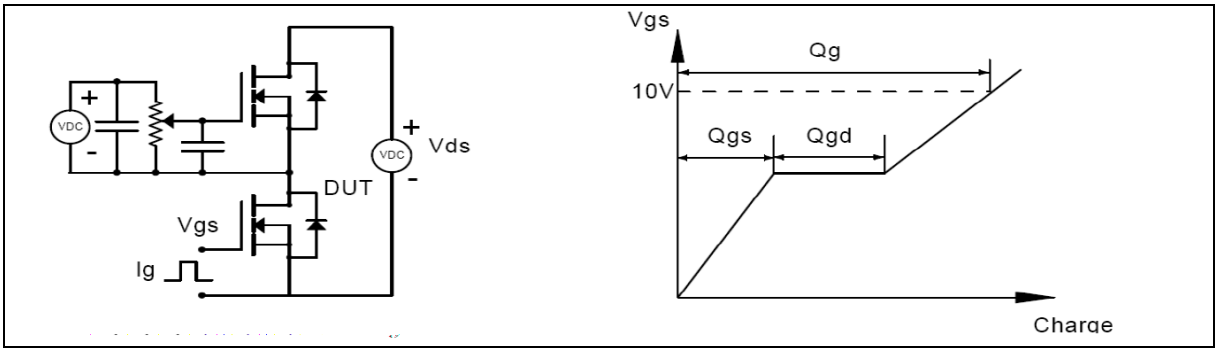


Figure 1. Gate charge test circuit & waveform

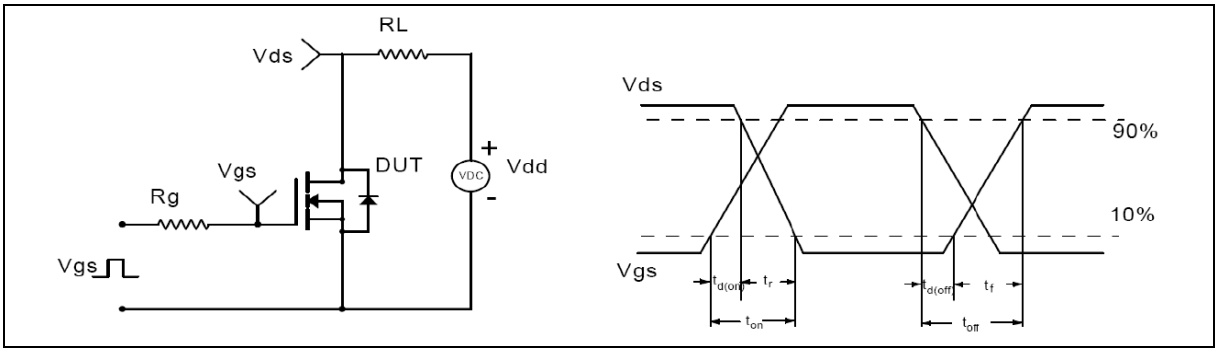


Figure 2. Switching time test circuit & waveforms

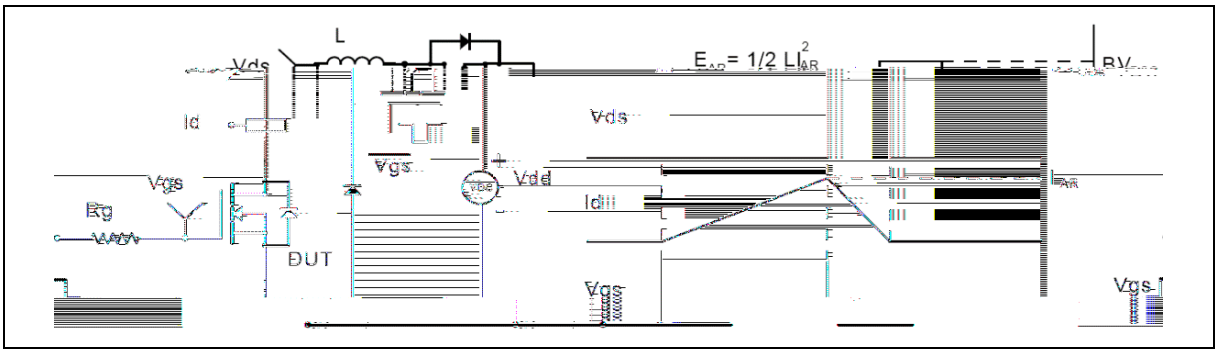


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

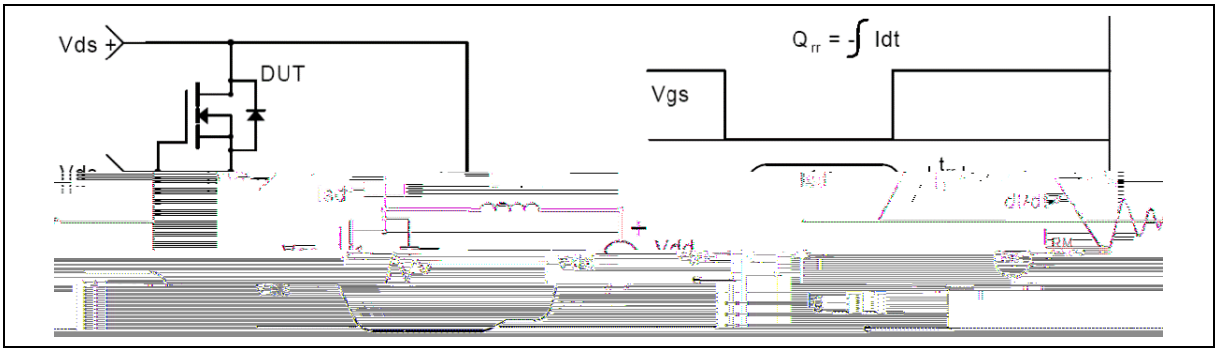
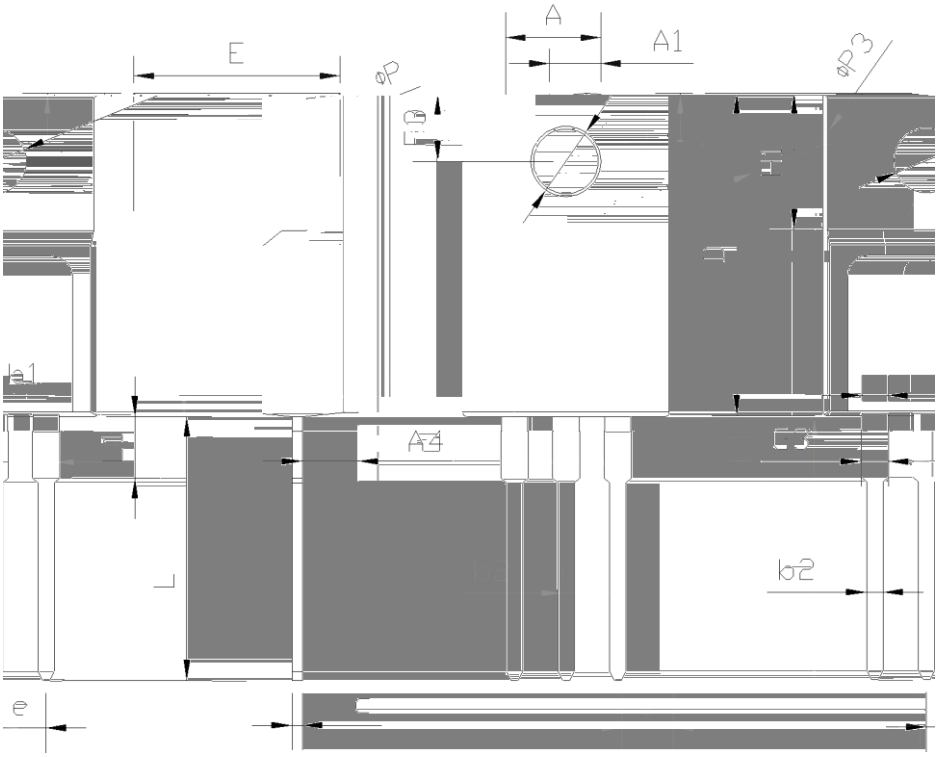


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
D	15.57	15.87	16.17
H1	6.70 REF		
e	2.54 BSC		
L	12.68	12.98	13.28
L1	2.88	3.03	3.18
- 3	3.03	3.18	3.38
- 3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

Version1: TO220F-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220F-C	50	20	1000	6	6000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R200FF	TO220F	yes	yes	yes

Legal Disclaimer

7KH LQIRUPDWLRQ JLYHQ LQ WKLV GRFXPHQW VKDOO LQ QR H
FRQGLWLRQV FRQVWLWXWH DQ\ IRUP RI VSHFLILFDWLRQ WHUPV RU DQ\ H[DPSOHV RU KLQWV JLYH
Y DO X H V K H U H L Q G D Q G R U D Q \ L Q I R U P D W L R Q U H J D U G L Q W K H D S S
6 H P L F R Q G X F W R U V F O D L P V D Q \ D Q G O L D E
Z L W K R X W O L P L W D W L R Q Z L Q O L Q H P H Q W R I L Q W H O O H F W X D O S U R S H
S D U W \
) R U I X U W K H U L Q I R U P D W L R Q R Q W H F K Q R O R J \ G H O L Y H U \ W H U P
F R Q W D F W L W K 6 H P L F R Q G X F W R U V G H V L J Q V S H F L I L F D W L R Q V H P L F R P

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